

2N3866
2N3866A

**NPN SILICON
HIGH FREQUENCY TRANSISTOR**



TO-39 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3866 and 2N3866A are Silicon NPN RF Transistors, mounted in a hermetically sealed package, designed for high frequency amplifier and oscillator applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	55	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	3.5	V
Continuous Collector Current	I_C	0.4	A
Continuous Base Current	I_B	2.0	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	5.0	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	35	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEO}	$V_{CE}=28\text{V}$		20	μA
I_{CEV}	$V_{CE}=55\text{V}, V_{BE(OFF)}=1.5\text{V}$		0.1	mA
I_{CEV}	$V_{CE}=30\text{V}, V_{BE(OFF)}=1.5\text{V}, T_C=200^\circ\text{C}$		5.0	mA
I_{EBO}	$V_{EB}=3.5\text{V}$		0.1	mA
BV_{CER}	$I_C=5.0\text{mA}, R_{BE}=10\Omega$	55		V
BV_{CBO}	$I_C=500\mu\text{A}$	55		V
BV_{CEO}	$I_C=5.0\text{mA}$	30		V
BV_{EBO}	$I_E=100\mu\text{A}$	3.5		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=20\text{mA}$		1.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$ (2N3866)	10	200	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$ (2N3866A)	25	200	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=360\text{mA}$	5.0		
f_T	$V_{CE}=15\text{V}, I_C=50\text{mA}, f=200\text{MHz}$ (2N3866)	500		MHz
f_T	$V_{CE}=15\text{V}, I_C=50\text{mA}, f=200\text{MHz}$ (2N3866A)	800		MHz
C_{ob}	$V_{CB}=28\text{V}, I_E=0, f=1.0\text{MHz}$		3.0	pF
G_{PE}	$V_{CC}=28\text{V}, P_{out}=1.0\text{W}, f=400\text{MHz}$ (Figure 1)		10	dB
η	$V_{CC}=28\text{V}, P_{out}=1.0\text{W}, f=400\text{MHz}$ (Figure 1)		45	%

R2 (15-September 2010)

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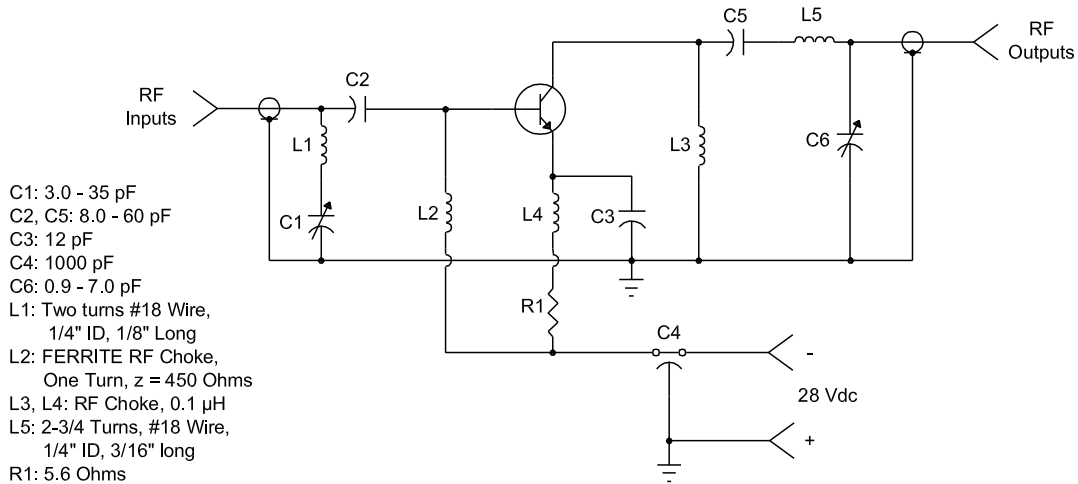
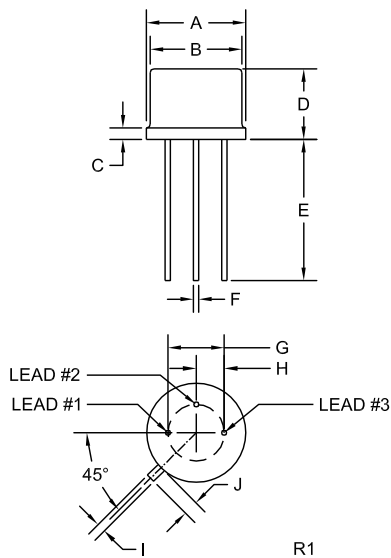


Figure 1. 400MHz Test Circuit

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R2 (15-September 2010)

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